

**P-CHANNEL MOS FIELD EFFECT TRANSISTOR
FOR SWITCHING**

DESCRIPTION

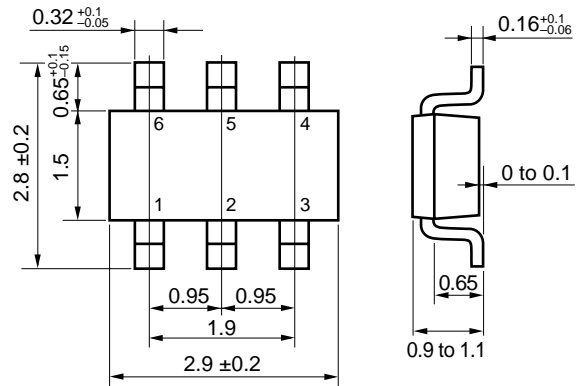
The μ PA1917 is a switching device which can be driven directly by a 1.8 V power source.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 1.8 V drive available
- Low on-state resistance
 $R_{DS(on)1} = 53 \text{ m}\Omega \text{ MAX. (} V_{GS} = -4.5 \text{ V, } I_D = -3.0 \text{ A)}$
 $R_{DS(on)2} = 70 \text{ m}\Omega \text{ MAX. (} V_{GS} = -2.5 \text{ V, } I_D = -3.0 \text{ A)}$
 $R_{DS(on)3} = 107 \text{ m}\Omega \text{ MAX. (} V_{GS} = -1.8 \text{ V, } I_D = -1.5 \text{ A)}$

PACKAGE DRAWING (Unit : mm)



1, 2, 5, 6 : Drain
3 : Gate
4 : Source

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA1917TE	SC-95 (Mini Mold Thin Type)

Marking : TR

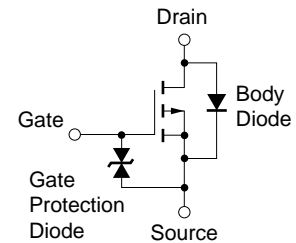
ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	-20	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±8.0	V
Drain Current (DC) (T _A = 25°C)	I _{D(DC)}	±6.0	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	±24	A
Total Power Dissipation	P _{T1}	0.2	W
Total Power Dissipation ^{Note2}	P _{T2}	2.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

- Notes 1.** PW ≤ 10 μs, Duty Cycle ≤ 1%
2. Mounted on FR-4 board, t ≤ 5 sec.

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

EQUIVALENT CIRCUIT

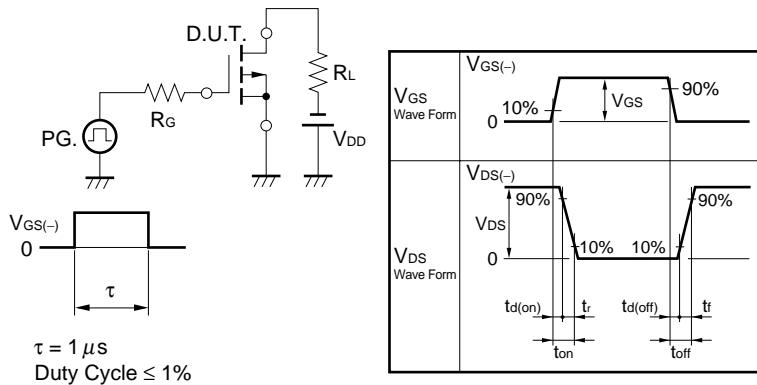


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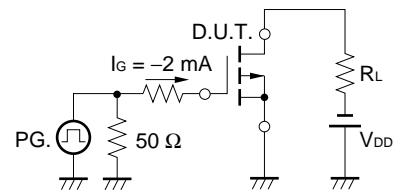
ELECTRICAL CHARACTERISTICS (T_A = 25°C)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20 V, V _{GS} = 0 V			-10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±8.0 V, V _{DS} = 0 V			±10	μA
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1.0 mA	-0.45	-0.75	-1.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} = -10 V, I _D = -3.0 A	5.0	10.4		S
Drain to Source On-state Resistance	R _{DS(on)1}	V _{GS} = -4.5 V, I _D = -3.0 A		42	53	mΩ
	R _{DS(on)2}	V _{GS} = -2.5 V, I _D = -3.0 A		52	70	mΩ
	R _{DS(on)3}	V _{GS} = -1.8 V, I _D = -1.5 A		64	107	mΩ
Input Capacitance	C _{iss}	V _{DS} = -10 V		835		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		170		pF
Reverse Transfer Capacitance	C _{rss}	f = 1.0 MHz		99		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = -10 V, I _D = -3.0 A		16		ns
Rise Time	t _r	V _{GS} = -4.0 V		64		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		78		ns
Fall Time	t _f			108		ns
Total Gate Charge	Q _G	V _{DD} = -16 V		8.1		nC
Gate to Source Charge	Q _{GS}	V _{GS} = -4.0 V		1.3		nC
Gate to Drain Charge	Q _{GD}	I _D = -6.0 A		2.8		nC
Diode Forward Voltage	V _{F(S-D)}	I _F = 6.0 A, V _{GS} = 0 V		0.94		V

TEST CIRCUIT 1 SWITCHING TIME

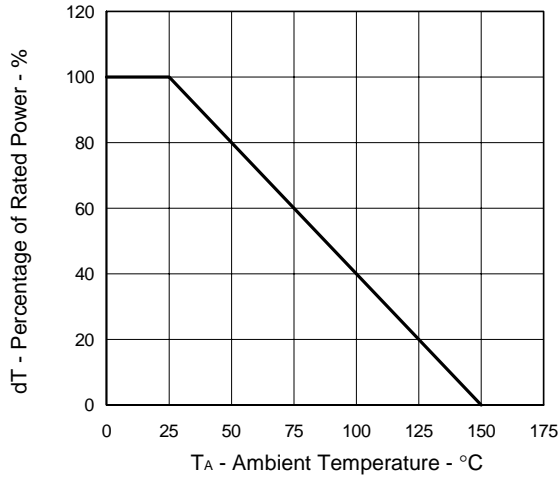


TEST CIRCUIT 2 GATE CHARGE

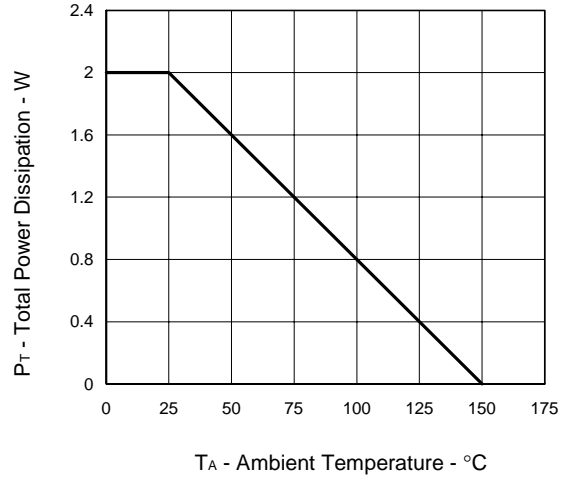


TYPICAL CHARACTERISTICS (T_A = 25°C)

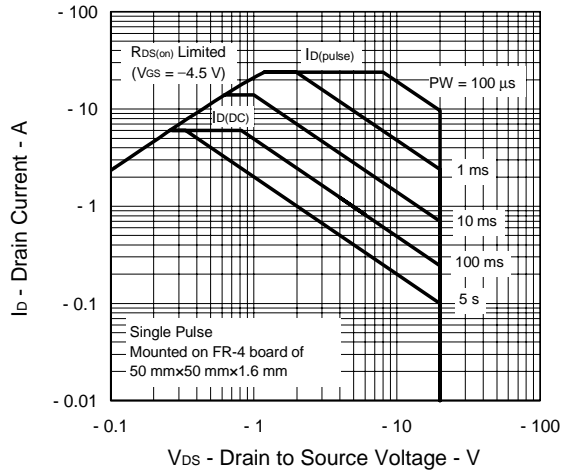
DERATING FACTOR FORWARD BIAS SAFE OPERATING AREA



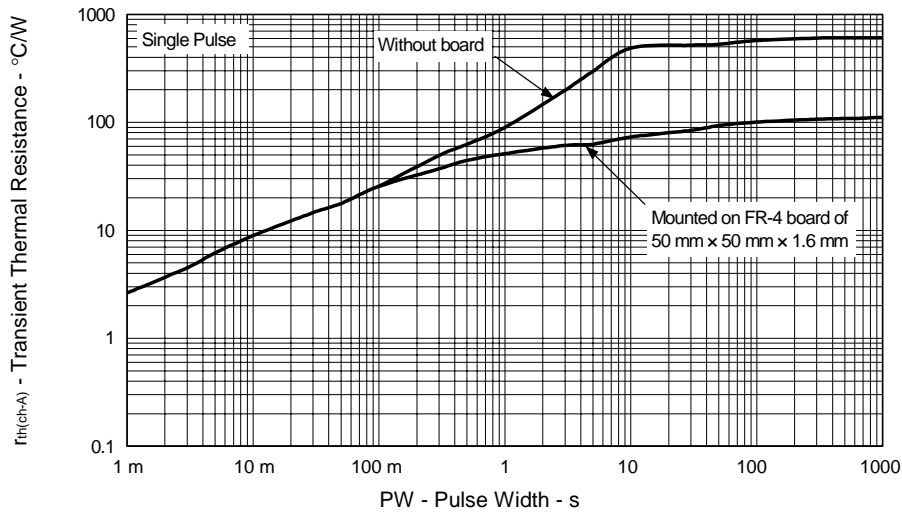
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



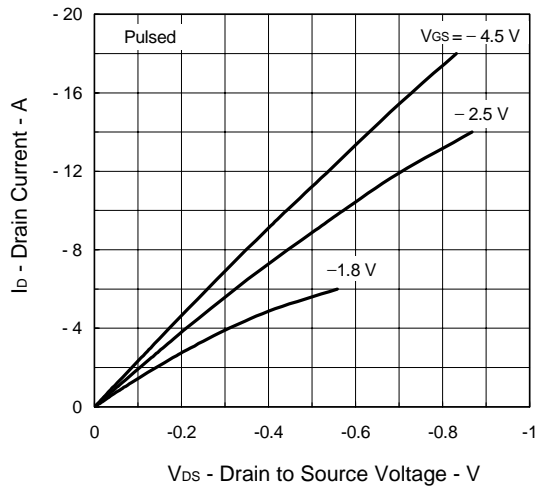
FORWARD BIAS SAFE OPERATING AREA



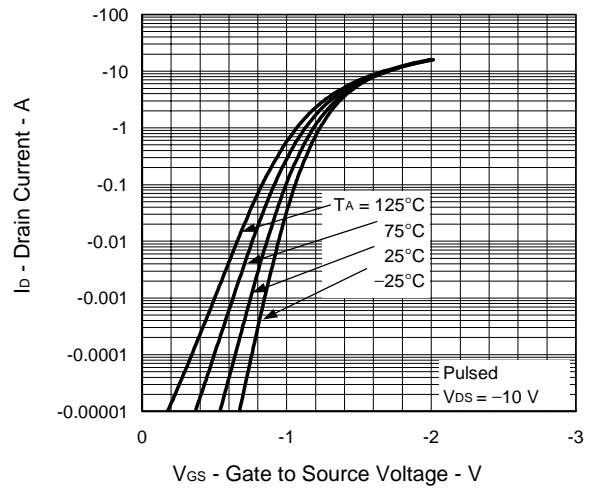
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



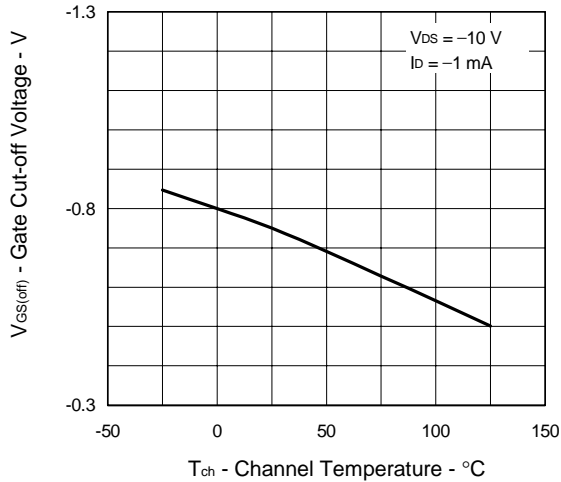
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



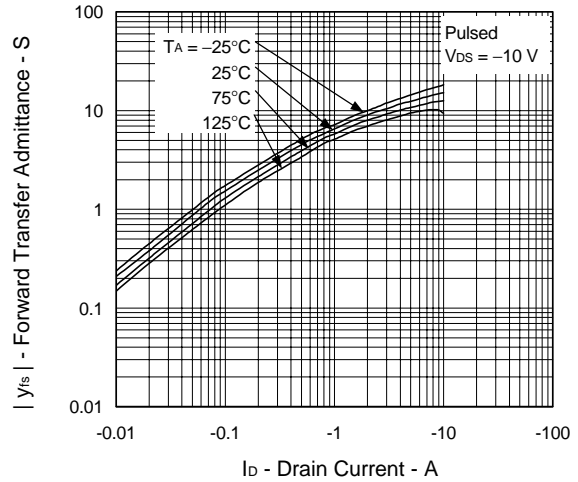
FORWARD TRANSFER CHARACTERISTICS



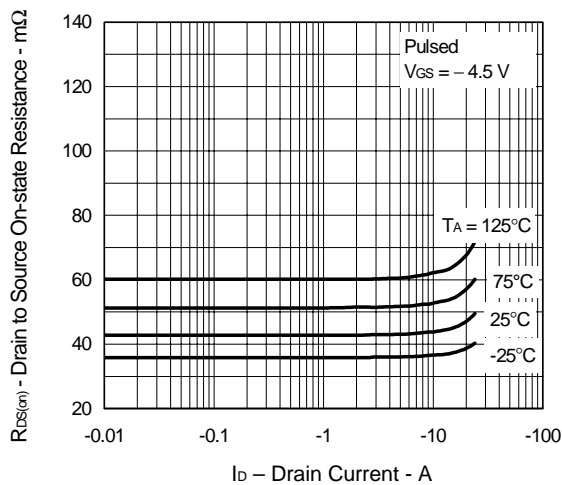
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



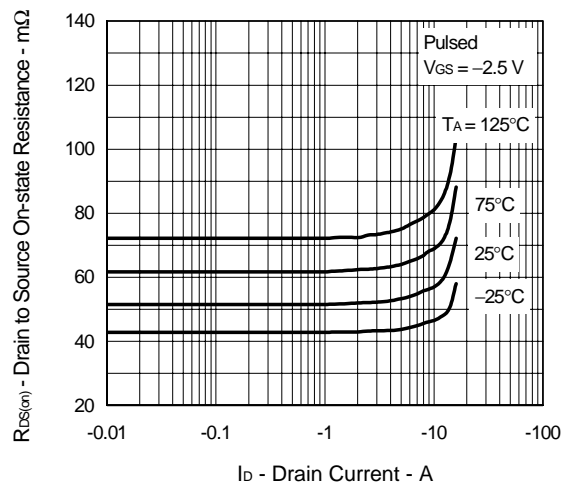
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



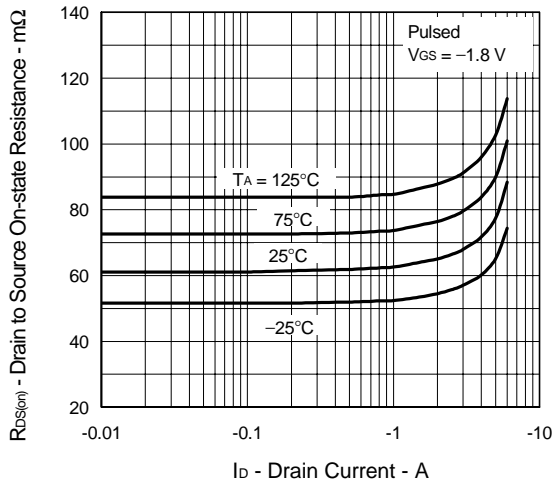
DRAIN TO SOURCE ON-STATE RESISTANCE vs DRAIN CURRENT



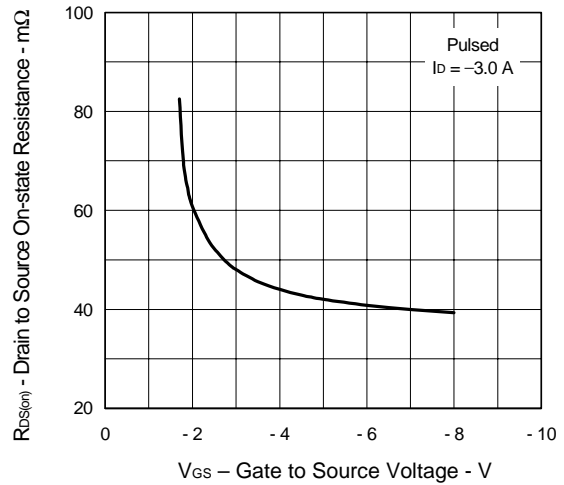
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



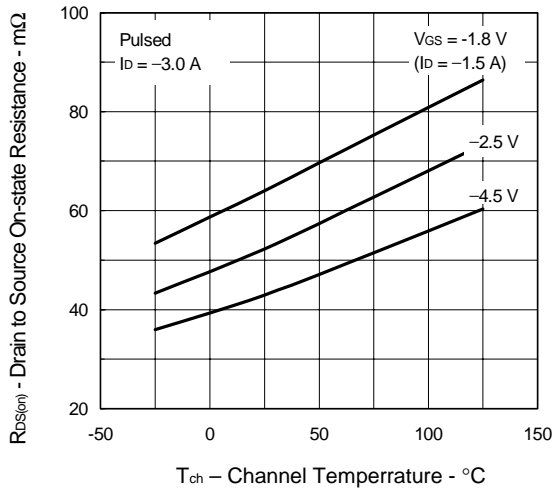
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



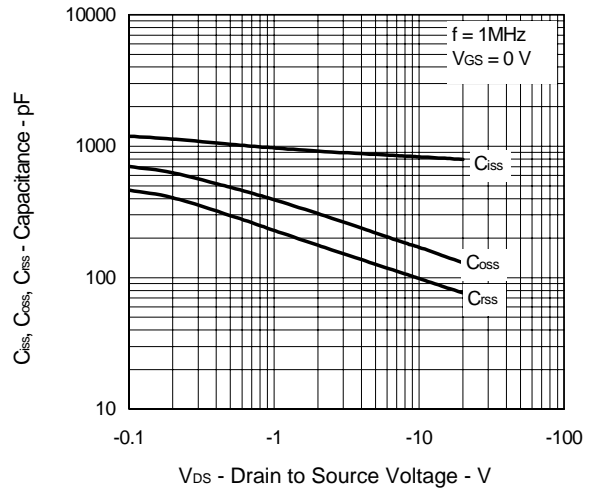
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



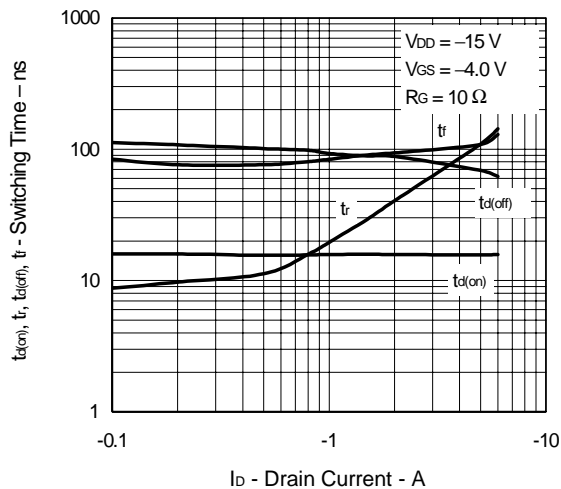
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



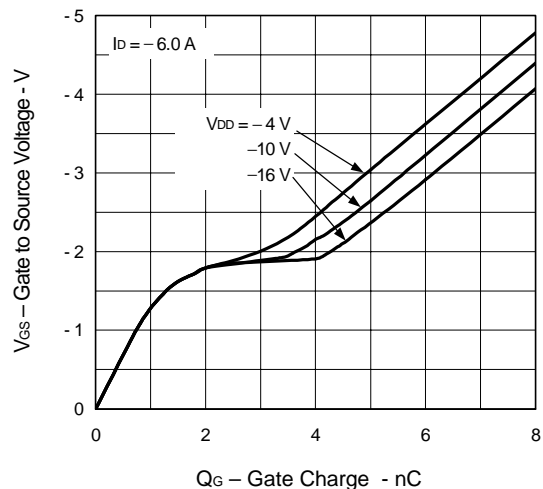
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

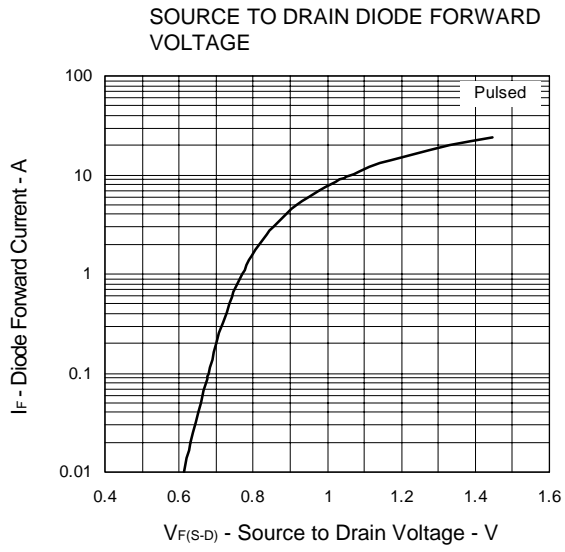


SWITCHING CHARACTERISTICS



DYNAMIC INPUT/OUTPUT CHARACTERISTICS





[MEMO]

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